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2N5876 (#23870)

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Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			1.00	V
DC Current Gain	HFE	20.00		100.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			80.00	V
Collector Current (dc)	I_C			10.00	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			80.00	V
Emitter-Base Voltage (Collector Open)	V_{EBO}			6.00	V
Power Dissipation, Total	P_T			150.00	W

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